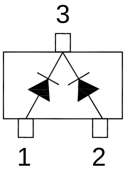
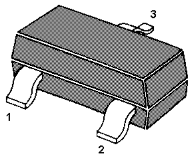
SB705D

SILICON EPITAXIAL PLANAR SCHOTTKY BARRIER DIODE

for general purpose detection and high speed
switching applications





Marking Code: **RB**
TO-236 Plastic Package

Absolute Maximum Ratings (T_a = 25 °C)

Parameter	Symbol	Value	Unit
Peak Reverse Voltage	V_{RM}	40	V
Reverse Voltage	V_R	40	V
Mean Rectifying Current	I_O	30	mA
Peak Forward Surge Current 1)	I_{FSM}	200	mA
Junction Temperature	T_j	125	°C
Storage Temperature Range	T_{stg}	- 40 to + 125	°C

1) 60 Hz for 1 ∿

Characteristics at T_a = 25 °C

Parameter	Symbol	Typ.	Max.	Unit
Forward Voltage at I_F = 1 mA	V_F	-	0.37	V
Reverse Current at V_R = 10 V	I_R	-	1	µA
Capacitance between Terminals at V_R = 1 V, f = 1 MHz	C_T	2	-	pF

Note: ESD sensitive product handling required.

®

Dated : 09/08/2006

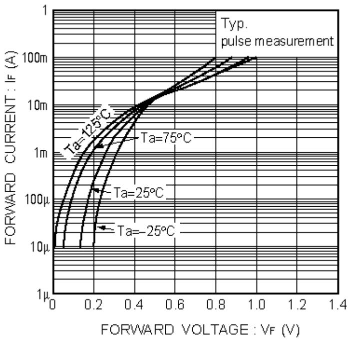


Fig. 1 Forward characteristics

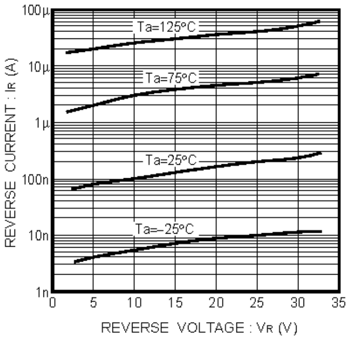


Fig. 2 Reverse characteristics

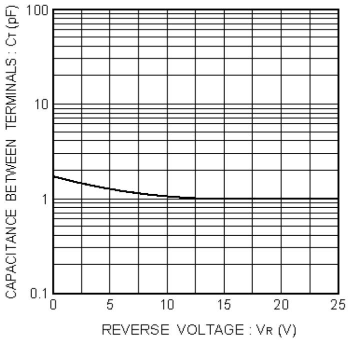


Fig. 3 Capacitance between terminals characteristics

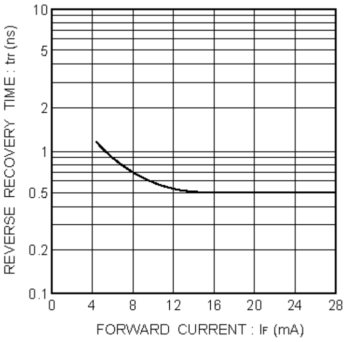


Fig. 4 Reverse recovery time characteristics

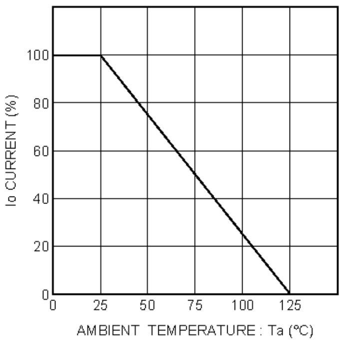


Fig. 5 Derating curve (mounting on glass epoxy PCBs)

Dated : 09/08/2006